

TQS0524P

The TQS0524P_ULC provides a typical line to line capacitance of 0.2pF between I/O pins and low insertion loss up to 3GHz providing greater signal integrity making it ideally suited for HDMI applications, such as Digital TVs, DVD players, Computing, set-top boxes and MDDI applications in mobile computing devices.

It has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from overvoltage caused by ESD(electrostatic discharge), CDE (Cable Discharge Events), and EFT (electrical fast transients).

Features

- Protects two or four I/O lines
- Low capacitance:0.2pf Typical between I/O channel
- Working voltages: 5V
- Low leakage current
- Response Time is < 1 ns
- Meets MSL 1 Requirements
- Solid-state silicon avalanche technology
- ROHS compliant
- TECHIP technology

Main applications

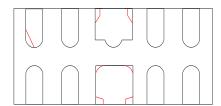
- High Definition Multi-Media Interface (HDMI1.3/1.4/2.0)
- Digital Visual Interface (DVI)
- Display Port Interface
- Serial ATA
- PCI Express
- USB 1.1/2.0/3.0/3.1/OTG
- IEEE 1394 Firewire Ports
- Projection TV Monitors and Flat Panel Displays
- Notebook Computers
- Set Top Box
- Projection TV

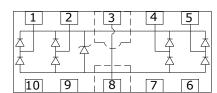
Protection solution to meet

- IEC61000-4-2 (ESD) ±15kV (air), ±8kV (contact)
- IEC61000-4-4 (EFT) 40A (5/50ns)



DFN2510





Ordering Information

Device	Qty per Reel	Reel Size
TQS0524P	3000	7 Inch



Typical electrical characterist applications Maximum ratings (Tamb=25°C Unless Otherwise Specified) **Parameter Symbol** Value Unit Peak Pulse Power (tp=8/20µs waveform) \mathbf{P}_{PPP} 55 Watts ESD Rating per IEC61000-4-2: Contact 20 KV 20 Air °C $T_{L} \\$ Lead Soldering Temperature 260 (10 sec.) °C Operating Temperature Range $T_{\rm J}$ -55 ~ 150 °C Storage Temperature Range Tstg -55 ~ 150

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

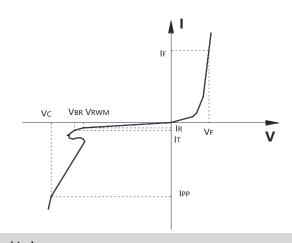
^{1.} Non-repetitive current pulse, per Figure 1.

Electrical characteristics (Tamb=25°C Unless Otherwise Specified)						
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$V_{\scriptscriptstyle \mathrm{RWM}}$	Reverse Working Voltage	Any I/O to Ground			5.0	V
$V_{\scriptscriptstyle BR}$	Reverse Breakdown Voltage	$I_T = 0.1\text{mA},$ Any I/O to Ground	6.0			V
$I_{\scriptscriptstyle R}$	Reverse Leakage Current	$V_{RWM} = 5V$, Any I/O to Ground			1	μΑ
$V_{\scriptscriptstyle F}$	Diode Forward Voltage	$I_F = 15 \text{mA}$		0.85	1.2	V
V _c	Clause's Wiles	$I_{PP} = 1A^{(1)}$, any I/O pin to Ground			6	V
	Clamping Voltage	$I_{PP} = 12A^{(1)}$, any I/O pin to Ground			12	V
R_{dyn}	dynamic resistance	positive transient(TLP) negative transient(TLP)		0.26 0.28		Ω
$C_{J}^{(2)}$	Junction Capacitance	$V_{IN} = 2.5V$, $f = 1MHz$, between I/O pins		0.20		pF
		V_{IN} = 2.5 V, f = 1MHz, any I/O pin to Ground		0.45	0.65	pF

 $Notes: (1) \textit{Measurements performed using a 100ns Transmission Line Pulse} (\textit{TLP}) \ \textit{system}.$

(2) Junction capacitance is measured in $V_R=0V, F=1MHz$

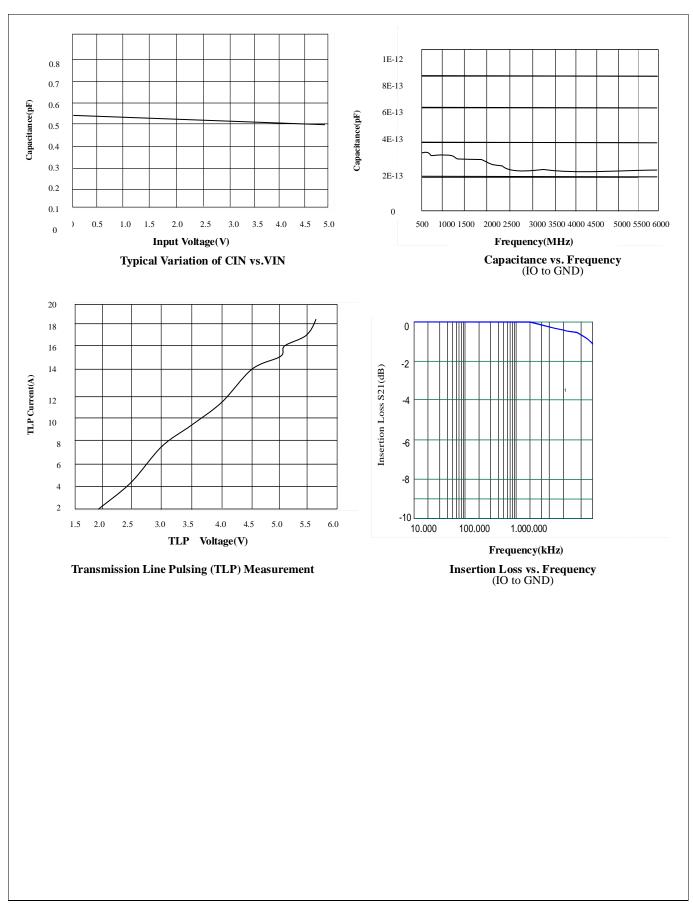
Symbol	Parameter		
$V_{\scriptscriptstyle \mathrm{RWM}}$	Working Peak Reverse Voltage		
$V_{\scriptscriptstyle BR}$	Breakdown Voltage @ IT		
Vc	Clamping Voltage @ IPP 100ns		
	Transmission Line Pulse(TLP)		
I_{T}	Test Current		
$\mathbf{I}_{\scriptscriptstyle{RM}}$	Leakage current at VRWM		
$\mathbf{I}_{\mathtt{PP}}$	Peak pulse current		
Co	Off-state Capacitance		
C_{J}	Junction Capacitance		



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^{*}Other voltages may be available upon request.







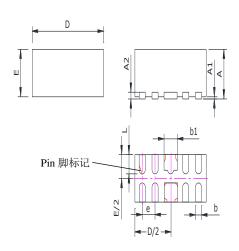
Package Information

DFN2510

Mechanical Data

Case:DFN2510

Case Material: Molded Plastic. UL Flammability



DIM	Millimeters			
DIM	Min	Max		
A	0.45	0.65		
A1	0.05REF			
A2	0.15REF			
b	0.15	0.25		
b1	0.30	0.50		
D	2.424	2.576		
E	0.924	1.076		
e	0.50REF			
L	0.30	0.45		

Recommended Pad outline

